

General Description

SFGMOS[®] low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The low V_{th} series is specially designed to use in synchronous rectification power systems with low driving voltage.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery



Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switched mode power supply

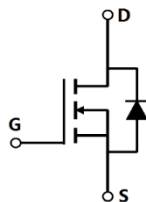
Key Performance Parameters

| Parameter | Value | Unit |
|-------------------------------|-------|------|
| $V_{DS, min} @ T_{j(max)}$ | 100 | V |
| $I_{D, pulse}$ | 32 | A |
| $R_{DS(ON) max} @ V_{GS}=10V$ | 20 | |
| Q_g | 19.8 | nC |

Marking Information

| Product Name | Package | Marking |
|--------------|---------|-----------|
| SFG10R20BF | SOP8 | SFG10R20B |

Package & Pin information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

| Parameter | Symbol | Value | Unit |
|---|----------------|------------|--------------------|
| Drain source voltage | V_{DS} | 100 | V |
| Gate source voltage | V_{GS} | ± 20 | V |
| Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$ | I_D | 8 | A |
| Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$ | $I_{D, pulse}$ | 32 | A |
| Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$ | I_S | 8 | A |
| Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$ | $I_{S, Pulse}$ | 32 | A |
| Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$ | P_D | 3.5 | W |
| Single pulsed avalanche energy ⁵⁾ | E_{AS} | 30 | mJ |
| Operation and storage temperature | T_{stg}, T_j | -55 to 150 | $^{\circ}\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Value | Unit |
|-----------------------------------|--------|-------|----------------------|
| Thermal resistance, junction-case | R | 35.7 | $^{\circ}\text{C/W}$ |

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test condition |
|----------------------------------|--------------|------|------|------|------|--|
| Drain-source breakdown voltage | BV_{DSS} | 100 | | | V | $V_{GS}=0\text{ V}, I_D=250\text{ A}$ |
| Gate threshold voltage | $V_{GS(th)}$ | 1.0 | | 2.5 | V | $V_{DS}=V_{GS}, I_D=250\text{ A}$ |
| Drain-source on-state resistance | $R_{DS(ON)}$ | | 17 | 20 | | $V_{GS}=10\text{ V}, I_D=8\text{ A}$ |
| Drain-source on-state resistance | $R_{DS(ON)}$ | | | 26 | | $V_{GS}=4.5\text{ V}, I_D=6\text{ A}$ |
| Gate-source leakage current | I_{GSS} | | | 100 | nA | $V_{GS}=20\text{ V}$ |
| | | | | -100 | | $V_{GS}=-20\text{ V}$ |
| Drain-source leakage current | I_{DSS} | | | 1 | A | $V_{DS}=100\text{ V}, V_{GS}=0\text{ V}$ |

Dynamic Characteristics 3 1 306.53 7ET~~CEMC~~ ~~q~~ ~~CEMC~~ ~~q~~ 6 Tm~~C~~ ~~q~~ 3 726.58 40.104T6 25 19.8 p n
Parameter **Symbol** **Min.**

Electrical Characteristics Diagrams

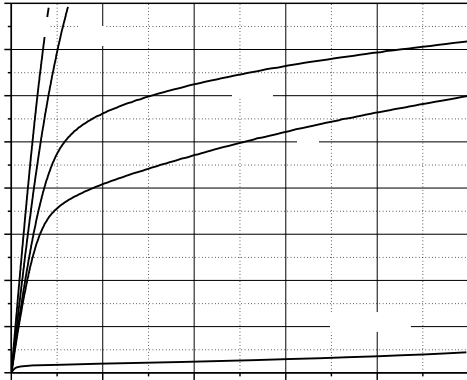


Figure 1. Typ. output characteristics

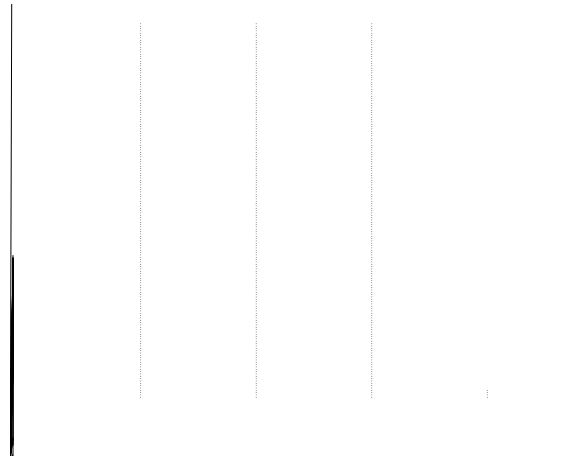


Figure 2. Typ. transfer characteristics

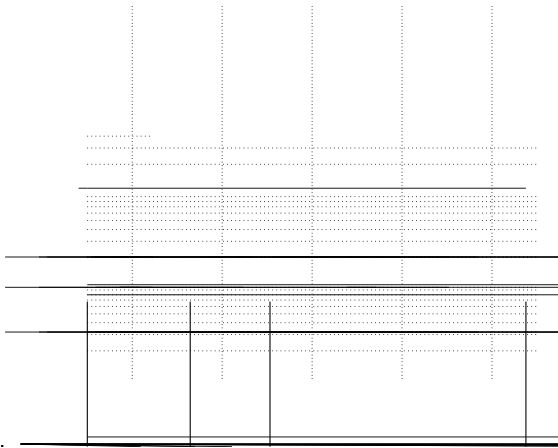


Figure 3. Typ. capacitances



Figure 4. Typ. gate charge

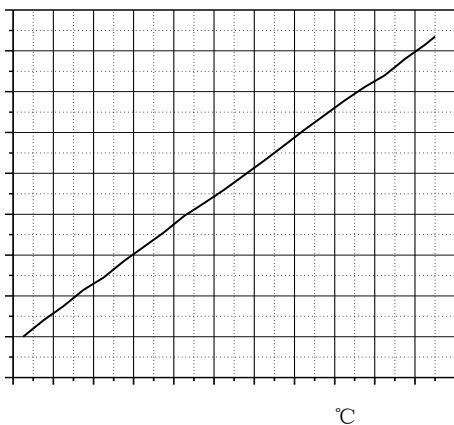


Figure 5. Drain-source breakdown voltage

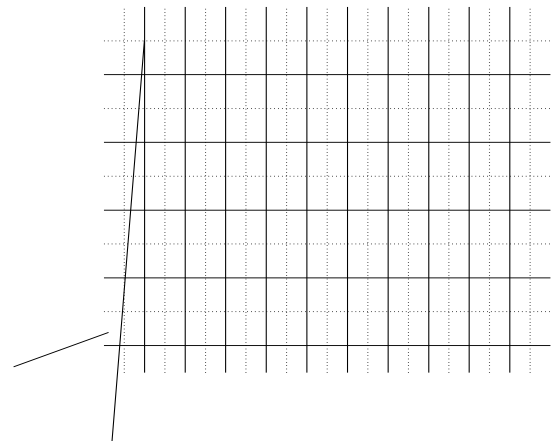
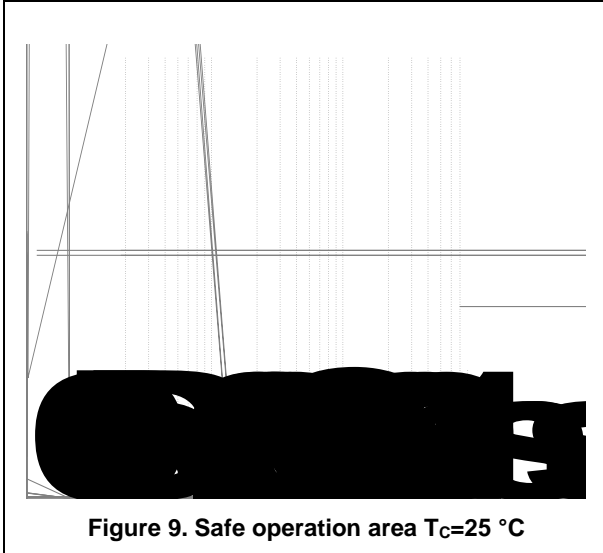
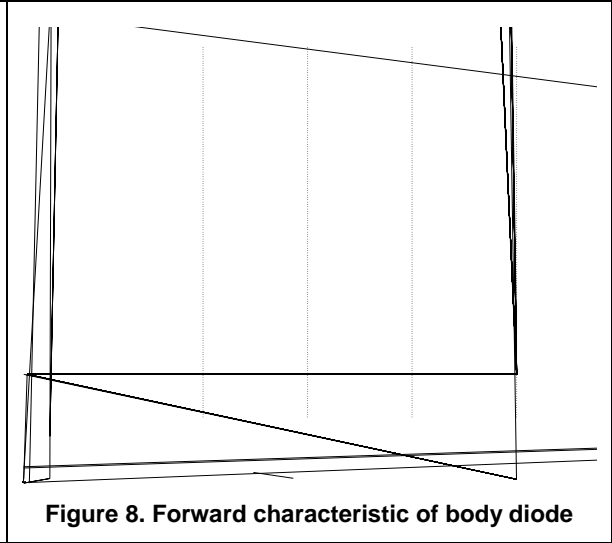
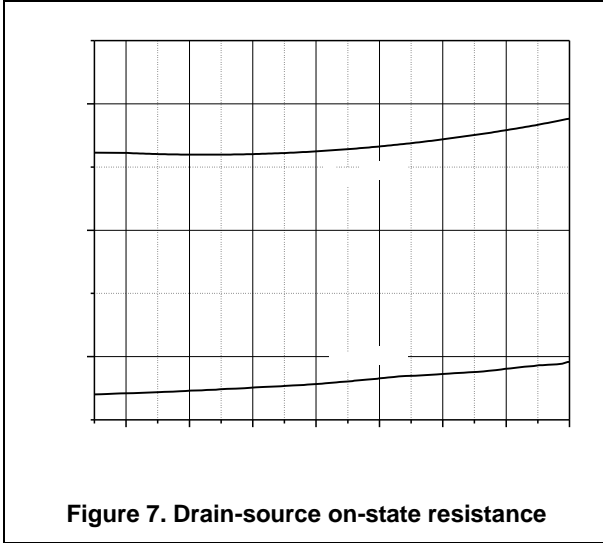


Figure 6. Drain-source on-state resistance



Test circuits and waveforms

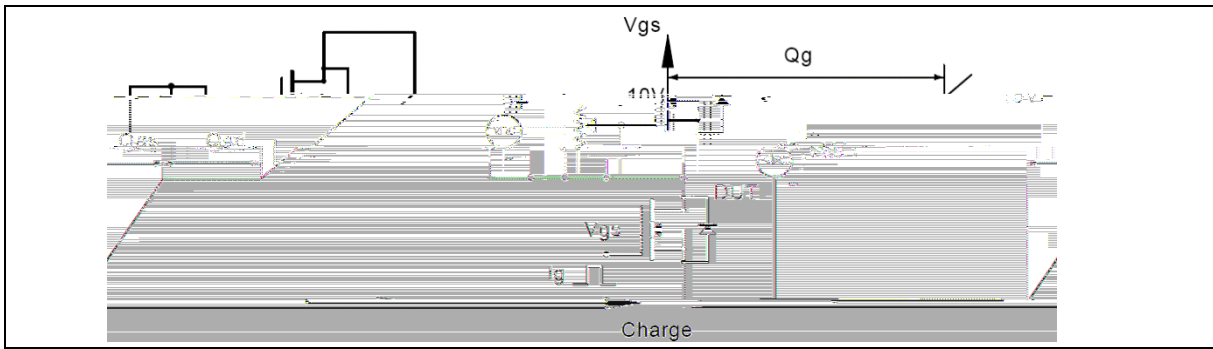


Figure 1. Gate charge test circuit & waveform

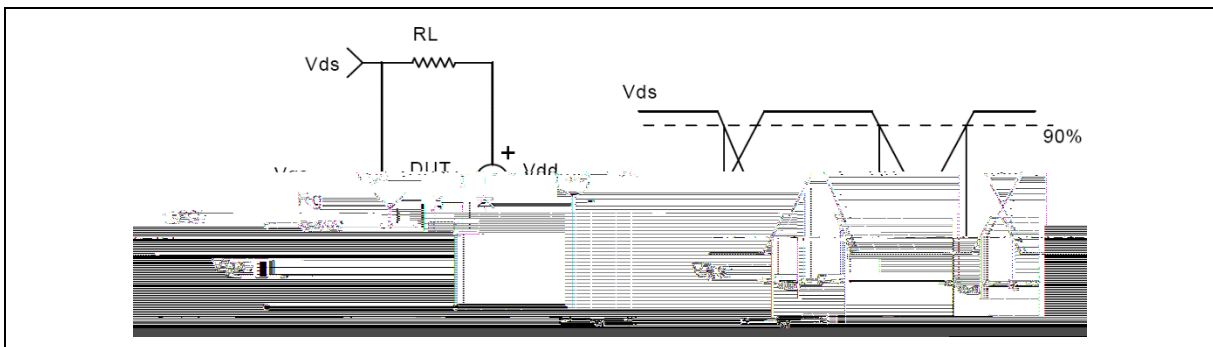


Figure 2. Switching time test circuit & waveforms

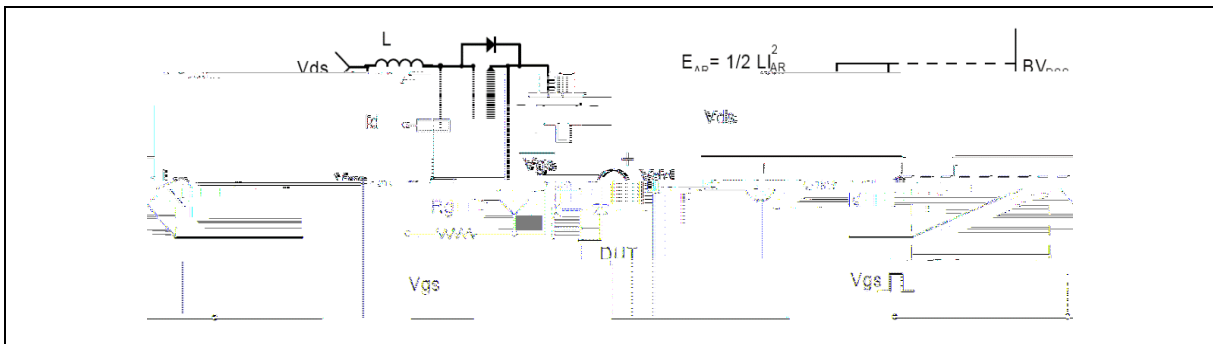


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

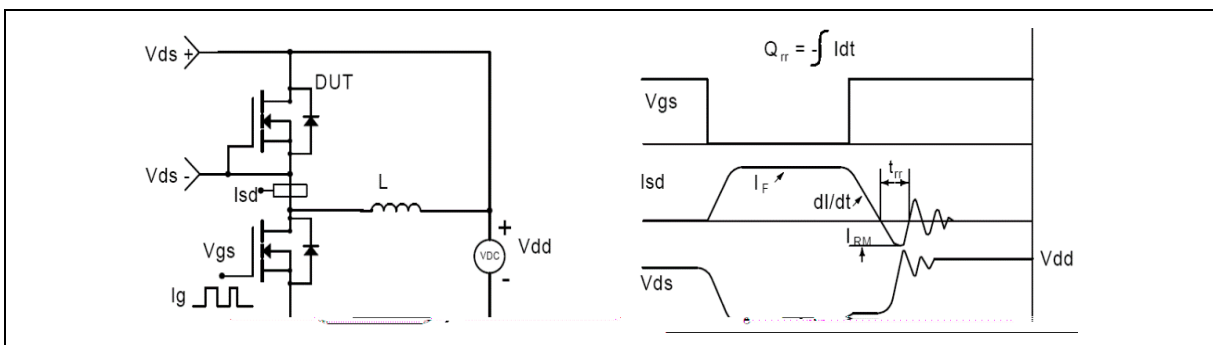
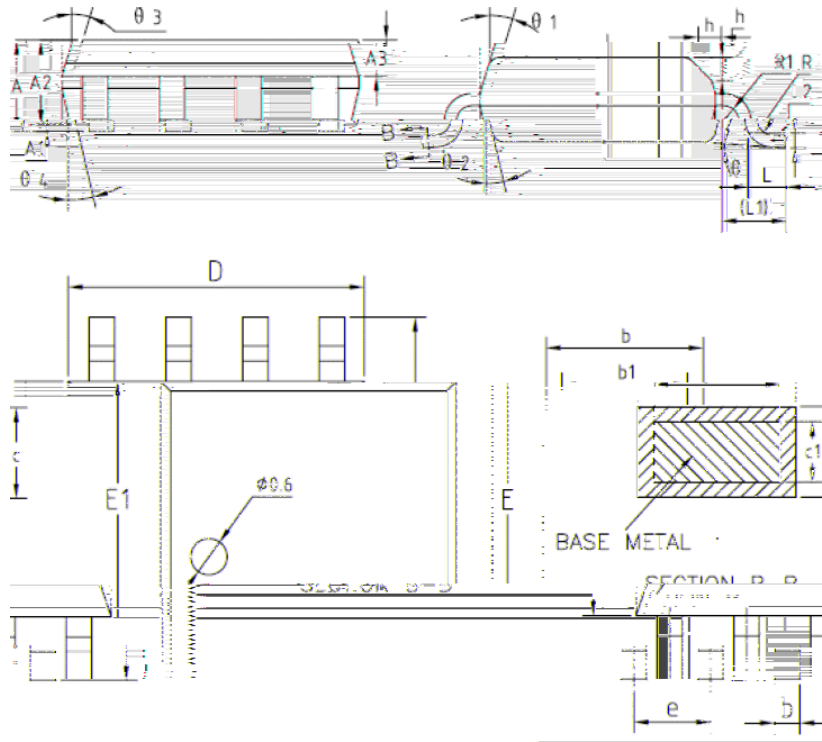


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



| Symbol | mm | | |
|--------|---------|------|------|
| | Min | Nom | Max |
| A | 1.35 | 1.55 | 1.75 |
| A1 | 0.10 | 0.15 | 0.25 |
| A2 | 1.25 | 1.40 | 1.65 |
| A3 | 0.50 | 0.60 | 0.70 |
| b | 0.38 | - | 0.51 |
| L1 | 1.04REF | | |
| L2 | 0.25BSC | | |
| b1 | 0.37 | 0.42 | 0.47 |
| c | 0.18 | - | 0.25 |
| c1 | 0.17 | 0.20 | 0.23 |
| D | 4.80 | 4.90 | 5 |
| E | 5.80 | 6.00 | 6.20 |
| E1 | 3.80 | 3.90 | 4.00 |
| e | 1.17 | 1.27 | 1.37 |
| L | 0.45 | 0.60 | 0.80 |
| R | 0.07 | - | - |
| R1 | 0.07 | - | - |
| h | 0.30 | 0.40 | 0.50 |
| (| 0 | - | / |
|) | (| (| (|
| | (| (| (|
| | ((| ((| ((|

Version 1: SOP8-K package outline dimension

Ordering Information

| Package Type | Units/ Reel | Reels / Inner Box | Units/ Inner Box | Inner Boxes/ Carton Box | Units/ Carton Box |
|--------------|-------------|-------------------|------------------|-------------------------|-------------------|
| SOP8-K | 2500 | 2 | 5000 | 6 | 30000 |

Product Information

| Product | Package | Pb Free | RoHS | Halogen Free |
|------------|---------|---------|------|--------------|
| SFG10R20BF | SOP8 | yes | yes | yes |

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